

P-Channel Enhancement Mode MOSFET

Description

The AO3407-HXY uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V.

This device is suitable for use as a Battery protection or in other Switching application.

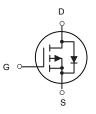


General Features

 V_{DS} = -30V, I_D = -4.1A $R_{DS(ON)}$ <60m Ω @ V_{GS} =10V

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3407-HXY	SOT23-3L	A7NV 1B	3000PCS

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	-30	V	
V _G s	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	-4.1	А	
Ірм	Drain Current-Pulsed (Note 1)	-13	Α	
P _D	Maximum Power Dissipation	1.32	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range -55 To 150		$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_D =-250uA	-30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.02		V/°C
Dagger	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3A		55	60	- mΩ
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-1.5A	-	90	98	
$V_{GS(th)}$	Gate Threshold Voltage	V V I- 2500A	-1.2	-1.5	-2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_{D}=-250uA$		4.32		mV/°C
la a a	Drain Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	
IDSS	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55°C			-5	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V_{DS} =-5 V , I_{D} =-3 A		4.8		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		24	48	Ω
Q_g	Total Gate Charge (-4.5V)			5.22	7.3	
Q_{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-3A		1.25	1.8	nC
Q_{gd}	Gate-Drain Charge			2.3	3.2	
T _{d(on)}	Turn-On Delay Time			18.4	37	
Tr	Rise Time	1		11.4	21	
$T_{d(off)}$	Turn-Off Delay Time			39.4	79	ns
T _f	Fall Time		5.2 10.4			
Ciss	Input Capacitance			463	650	
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		82	115	pF
C _{rss}	Reverse Transfer Capacitance			68	95	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current			-3.2	Α
Ism	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			-13	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1	V

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

^{3.}The power dissipation is limited by 150°C junction temperature

^{4.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

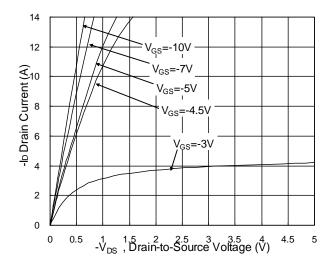


Fig.1 Typical Output Characteristics

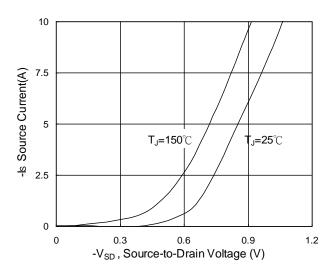


Fig.3 Source Drain Forward Characteristics

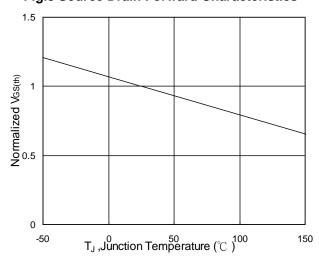


Fig.5 Normalized V_{GS(th)} vs. T_J

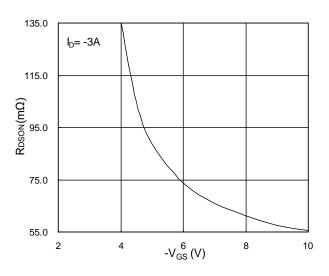


Fig.2 On-Resistance vs. G-S Voltage

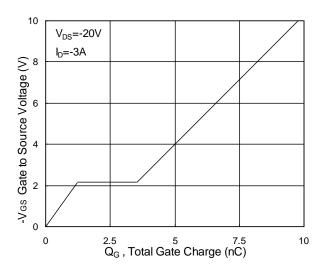


Fig.4 Gate-Charge Characteristics

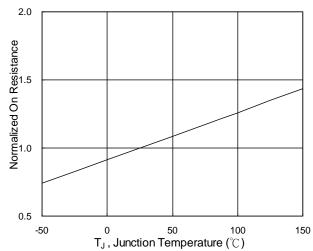
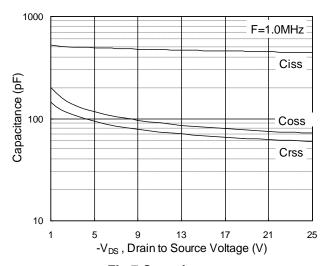


Fig.6 Normalized R_{DSON} vs. T_J





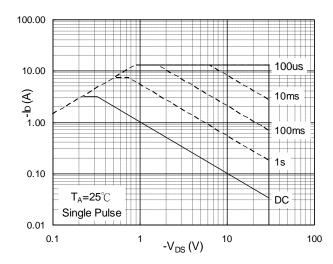


Fig.7 Capacitance

Fig.8 Safe Operating Area

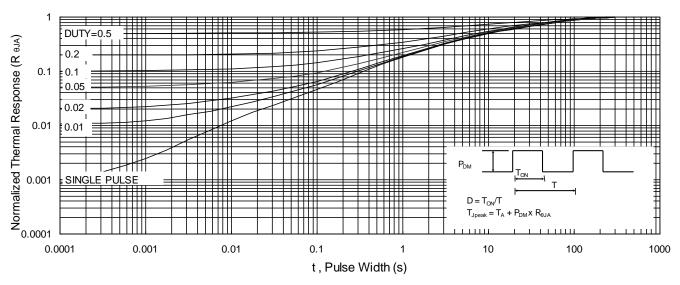
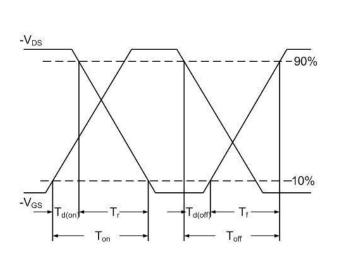


Fig.9 Normalized Maximum Transient Thermal Impedance



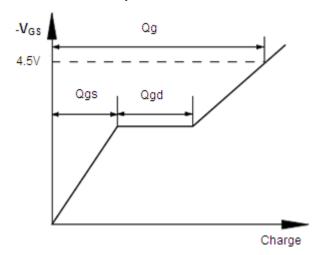
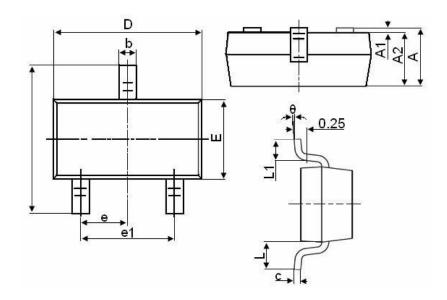


Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L		0.550REF	
L1	0.300	0.600	
θ	0°	8°	



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